


50. The method according to claim 39 wherein said second and third gate electrodes are formed by patterning a conductive layer, said conductive layer comprising a material selected from the group consisting of tantalum, chromium, titanium, tungsten, molybdenum, and silicon.--

REMARKS

The Official Action of August 26, 2002 was received and its contents carefully reviewed. In response, Applicants hereby elect without traverse Group II (claims 31 and 32) drawn to a process for making a semiconductor device classified in Class 438, subclass 1+, and cancel non-elected claims 17-30..

Consideration and allowance of the instant application are now respectfully requested.

Respectfully submitted,



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